G771H-US

Fig.1

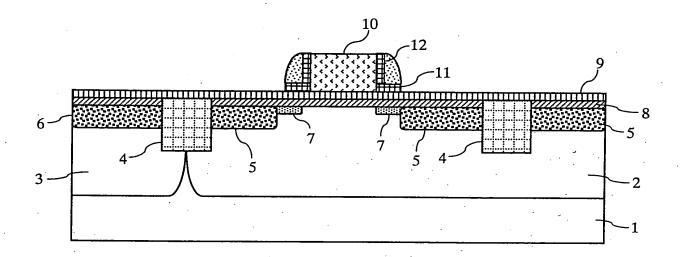


Fig.2A

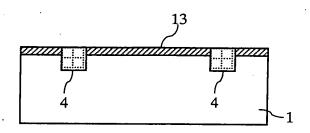


Fig.2B

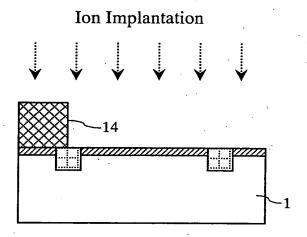


Fig.2C

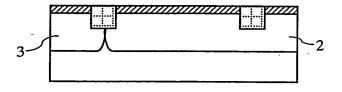


Fig.2D

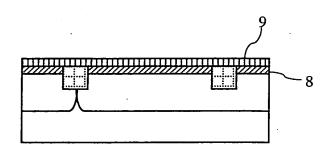


Fig.2E

Ion Implantation

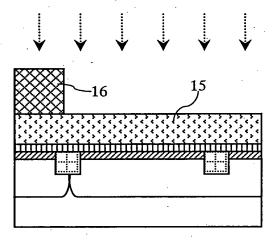


Fig.2F

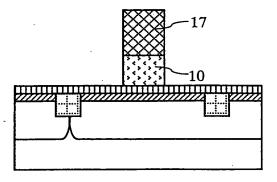


Fig.3A

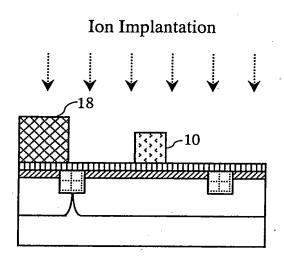
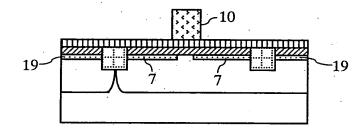


Fig.3B



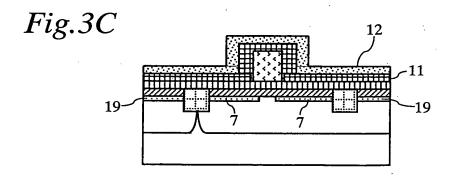


Fig.3D

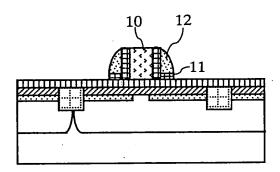


Fig.3E

Ion Implantation

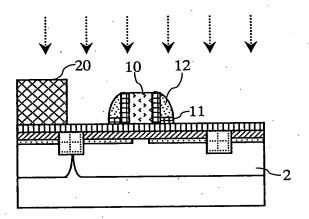


Fig.3F

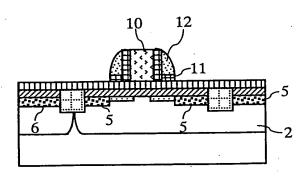
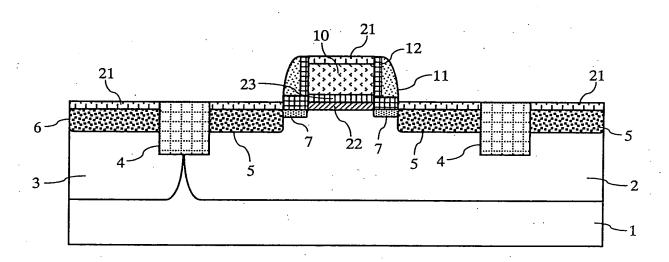
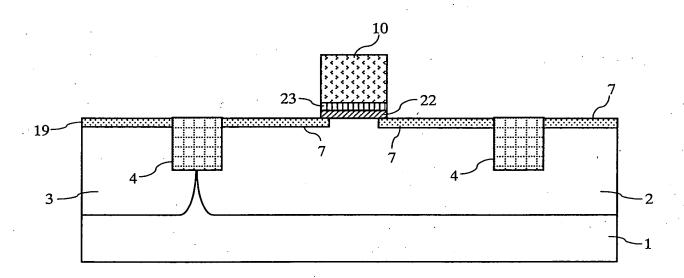
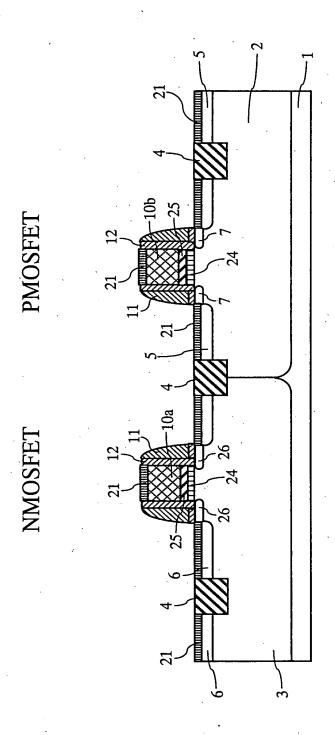


Fig.4







Title: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREFOR

Inventors: Tomonori AOYAMA Atty Docket No.: 403023 Leydig, Voit & Mayer 202-737-6770

Fig.7

